

# HIGH SPEED 1K X 8 DUAL-PORT STATIC SRAM

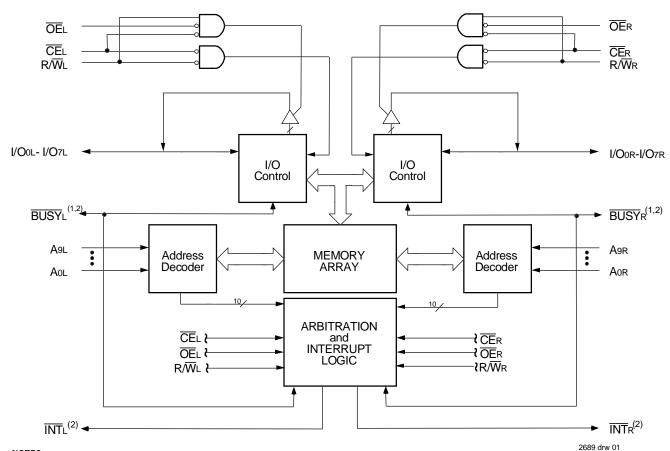
### IDT7130SA/LA IDT7140SA/LA

#### **Features**

- High-speed access
  - Military: 25/35/55/100ns (max.)
  - Industrial: 55/100ns (max.)
  - Commercial: 20/25/35/55/100ns (max.)
- Low-power operation
  - IDT7130/IDT7140SA
    - Active: 550mW (typ.)
    - Standby: 5mW (typ.)
  - IDT7130/IDT7140LA
    - Active: 550mW (typ.)
  - Standby: 1mW (typ.)
- MASTER IDT7130 easily expands data bus width to 16-ormore-bits using SLAVE IDT7140

- On-chip port arbitration logic (IDT7130 Only)
- ◆ BUSY output flag on IDT7130; BUSY input on IDT7140
- INT flag for port-to-port communication
- Fully asynchronous operation from either port
- Battery backup operation-2V data retention (LA only)
- ◆ TTL-compatible, single 5V ±10% power supply
- Military product compliant to MIL-PRF-38535 QML
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in 48-pin DIP and LCC, 52-pin PLCC, and 64-pin STQFP and TQFP

### **Functional Block Diagram**



#### NOTES

- IDT7130 (MASTER): BUSY is open drain output and requires pullup resistor. IDT7140 (SLAVE): BUSY is input.
- 2. Open drain output: requires pullup resistor.

**JUNE 2000** 

©2000 Integrated Device Technology, Inc.

DSC-2689/10

### **Description**

The IDT7130/IDT7140 are high-speed 1K x 8 Dual-Port Static RAMs. The IDT7130 is designed to be used as a stand-alone 8-bit Dual-Port RAM or as a "MASTER" Dual-Port RAM together with the IDT7140 "SLAVE" Dual-Port in 16-bit-or-more word width systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 16-or-more-bit memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

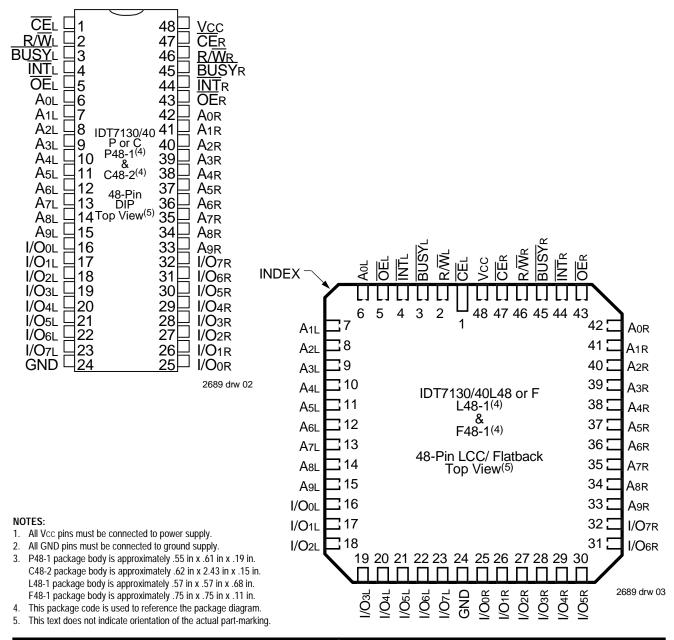
Both devices provide two independent ports with separate control, address, and I/O pins that permit independent asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by  $\overline{\text{CE}}$ , permits the on chip circuitry

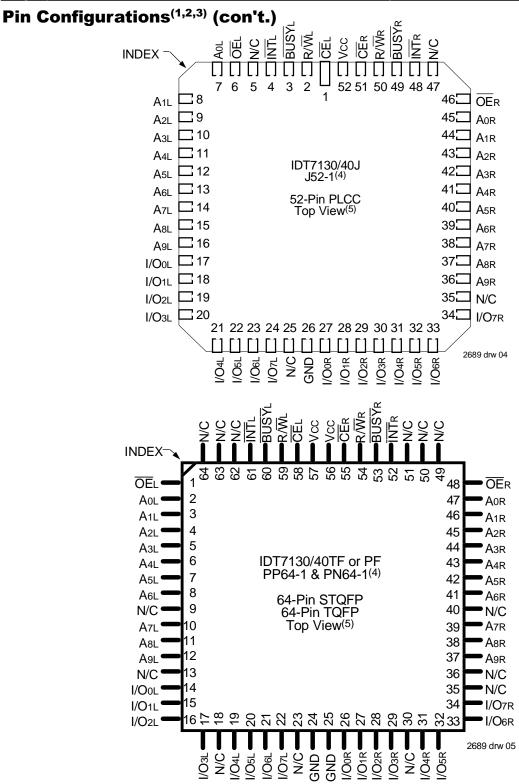
of each port to enter a very low standby power mode.

Fabricated using IDT's CMOS high-performance tech-nology, these devices typically operate on only 550mW of power. Low-power (LA) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200µW from a 2V battery.

The IDT7130/IDT7140 devices are packaged in 48-pin sidebraze or plastic DIPs, LCCs, flatpacks, 52-pin PLCC, and 64-pin TQFP and STQFP. Military grade products are manufactured in compliance with the latest revision of MIL-PRF-38535 QML, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

## Pin Configurations (1,2,3)





#### NOTES:

- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- J52-1 package body is approximately .75 in x .75 in x .17 in. PP64-1 package body is approximately 10 mm x 10 mm x 1.4mm. PN64-1 package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

## Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Military	Unit
VTERM <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	٧
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	۰C
Tstg	Storage Temperature	-65 to +150	-65 to +150	۰C
ЮИТ	DC Output Current	50	50	mA

#### NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may
  cause permanent damage to the device. This is a stress rating only and functional
  operation of the device at these or any other conditions above those indicated in
  the operational sections of the specification is not implied. Exposure to absolute
  maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

#### Capacitance (TA = +25°C, f = 1.0MHz) STQFP and TQFP Packages Only

Symbol	Parameter <sup>(1)</sup>	Conditions	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	9	pF
Соит	Output Capacitance	Vout = 3dV	10	pF

#### NOTES:

- This parameter is determined by device characterization but is not production tested.
- 3dV references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

## Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.2	_	6.0(2)	V
VIL	Input Low Voltage	-0.5 <sup>(1)</sup>	_	0.8	V

#### NOTES

2689 tbl 01

2689 tbl 05

- 1. VIL (min.)  $\geq$  -1.5V for pulse width less than 10ns.
- 2. VTERM must not exceed Vcc + 10%.

## Recommended Operating Temperature and Supply Voltage<sup>(1,2)</sup>

Grade	Ambient Temperature	GND	Vcc
Military	-55°C to +125°C	0V	5.0V <u>+</u> 10%
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

#### NOTES:

- 1. This is the parameter Ta. This is the "instant on" case temperature.
- Industrial temperature: for specific speeds, packages and powers contact your sales office.

## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 5.0V ± 10%)

_			7130SA 7140SA		7130LA 7140LA		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
lu	Input Leakage Current <sup>(1)</sup>	VCC = 5.5V, $VIN = 0V$ to $VCC$	_	10	_	5	μA
llo	Output Leakage Current <sup>(1)</sup>	$\frac{V_{CC}}{CE}$ = V <sub>H</sub> , V <sub>OUT</sub> = 0V to V <sub>CC</sub>	_	10	_	5	μA
Vol	Output Low Voltage (I/Oo-I/O7)	IoL = 4mA	_	0.4	-	0.4	V
Vol	Open Drain O <u>utput</u> Low Voltage (BUSY, INT)	loL = 16mA	_	0.5		0.5	V
Voh	Output High Voltage	IOH = -4mA	2.4	_	2.4	_	V

#### NOTE:

1. At  $Vcc \le 2.0V$  leakages are undefined.

2689 tbl 04

2689 tbl 02

## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1,5,7)</sup> (Vcc = 5.0V ± 10%)

					7130) 7140) Com'l	(20(2)	7140 Com		7140	0X35 0X35 n'l & tary	
Symbol	Param eter	Test Condition	Versi	on	Тур.	Max.	Тур.	Max.	Тур.	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	$\overline{CE}_L$ and $\overline{CE}_R = V_{IL}$ , Outputs Disabled $f = fMAX^{(S)}$	COM'L	SA LA	110 110	250 200	110 110	220 170	110 110	165 120	m A
	(Both Forts Active)	I = IMAX**	MIL & IND	SA LA			110 110	280 220	110 110	230 170	
I <sub>SB1</sub>	Standby Current (Both Ports - TTL Level Inputs)	$\overline{CE}_{L}$ and $\overline{CE}_{R} = V_{IH}$ f = fMAX <sup>(3)</sup>	COM'L	SA LA	30 30	65 45	30 30	65 45	25 25	65 45	m A
	Lever inputs)		MIL & IND	S A L A			30 30	80 60	25 25	80 60	
ISB2	Standby Current (One Port - TTL Level Inputs)	CEA* = VIL and CE'B* = VIH <sup>(6)</sup> Active Port OutputsDisabled,	COM'L	S A L A	65 65	165 125	65 65	150 115	50 50	125 90	m A
	Level ilipuis)	f=fmax <sup>(3)</sup>	MIL & IND	SA LA	-		65 65	160 125	50 50	150 115	
I <sub>SB3</sub>	Full Standby Current (Both Ports -	CE <sub>1</sub> and CE <sub>R</sub> ≥ V <sub>CC</sub> - 0.2V,	COM'L	S A L A	1.0 0.2	15 5	1.0 0.2	15 5	1.0 0.2	15 4	m A
	CMOS Level Inputs)	Inputs) $ \begin{array}{c} V_{IN} \geq V_{CC} \cdot 0.2V \text{ or} \\ V_{IN} \leq 0.2V, \ f = \ 0^{(4)} \end{array} $	MIL & IND	SA LA	_		1.0 0.2	30 10	1.0 0.2	30 10	
ISB4	Full Standby Current (One Port -	<u>CE</u> 'A" ≤ 0.2V and <u>CE</u> 'B" ≥ VCC - 0.2V <sup>(6)</sup>	COM'L	S A L A	60 60	155 115	60 60	145 105	45 45	110 85	m A
	CMOS Level Inputs)	el Inputs) $V_N \ge \overline{V_{CC}} - 0.2V$ or $V_N \le 0.2V$ Active Port Outputs Disabled, $f = f_{MAX}^{(0)}$	MIL & IND	S A L A			60 60	155 115	45 45	145 105	

2689 tbl 06a

				714 Com	0X55 0X55 'I, Ind ilitary	7140 Com'	X100 X100 I, Ind Iitary	
Symbol	Param eter Param eter	Test Condition	Version	Тур.	Max.	Тур.	Max.	Unit
lcc	Dynamic Operating Current (Both Ports Active)	$\overline{CE}_L$ and $\overline{CE}_R = V_{IL}$ , Outputs Disabled $f = fMAX^{(3)}$	COM'L SA	110 110	155 110	110 110	155 110	m A
	(BUIII PUIS ACIIVE)	I = IMAX <sup>∞</sup> /	MIL & SA		190 140	110 110	190 140	
I <sub>SB1</sub>	Standby Current (Both Ports - TTL Level Inputs)	f = fMAX <sup>(0)</sup>	COM'L SA	20 20	65 35	20 20	55 35	m A
	Lever inputs)		MIL & SA IND LA	20 20	65 45	20 20	65 45	
ISB2	Standby Current (One Port - TTL Level Inputs)	CEA* = VIL and CE'B* = VIH <sup>(6)</sup> Active Port Outputs Disabled, f=Max <sup>(6)</sup>	COM'L SA	40 40	110 75	40 40	110 75	m A
	Level inputs)	I=IMAX	MIL & SA	40 40	125 90	40 40	125 90	
ISB3	Full Standby Current (Both Ports - CMOS Level Inputs)	CE <sub>1</sub> and CE <sub>R</sub> ≥ Vcc - 0.2V,	COM'L SA	1.0 0.2	15 4	1.0 0.2	15 4	m A
	GWO3 Level IIIpuis)	$V \text{ IN } \ge V \text{ CC } - 0.2 V \text{ or } V \text{ IN } \le 0.2 V \text{, } f = 0^{(4)}$	MIL & SA	1.0 0.2	30 10	1.0 0.2	30 10	
ISB4	(One Port - $\overline{CE}^*B^* > VCC - 0.2V^{(6)}$	$\overline{CE}$ "B" $\geq VCC - 0.2V^{(6)}$	COM'L SA	40 40	100 70	40 40	95 70	m A
	CMOS Level Inputs)	$V_{NN} \ge V_{CC}$ - 0.2V or $V_{NN} \le 0.2V$ Active Port Outputs Disabled, $f = f_{MAX}^{(S)}$	MIL & SA	40 40	110 85	40 40	110 80	

#### NOTES:

2689 tb106b

- 1. 'X' in part numbers indicates power rating (SA or LA).
- 2. PLCC and TQFP packages only.
- 3. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/tcyc, and using "AC TEST CONDITIONS" of input levels of GND to 3V.
- 4. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.
- 5. Vcc = 5V, Ta=+25°C for Typ and is not production tested. Vcc DC = 100 mA (Typ)
- 6. Port "A" may be either left or right port. Port "B" is opposite from port "A".
- 7. Industrial temperature: for other speeds, packages and powers contact your sales office.

**Data Retention Characteristics (LA Version Only)** 

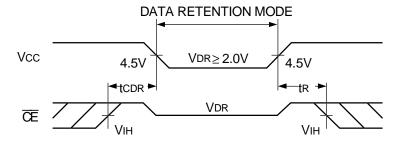
				7130LA/7140LA			
Symbol	Parameter	Test Condition		Min.	Typ. <sup>(1)</sup>	Max.	Unit
VDR	Vcc for Data Retention			2.0	_	_	V
ICCDR	Data Retention Current	1	MIL. & IND.	_	100	4000	μΑ
		$Vcc = 2.0V, \overline{CE} \ge Vcc -0.2V$	COM'L.	_	100	1500	
tcdr(3)	Chip Deselect to Data Retention Time	$Vin \ge Vcc -0.2V \text{ or } Vin \le 0.2V$		0	_	_	ns
tr(3)	Operation Recovery Time	]		trc <sup>(2)</sup>	_	_	ns

2689 tb107

#### NOTES:

- 1. Vcc = 2V, TA = +25°C, and is not production tested.
- 2. trc = Read Cycle Time
- 3. This parameter is guaranteed but not production tested.

### **Data Retention Waveform**



2692 drw 06

### **AC Test Conditions**

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

2689 tbl 08

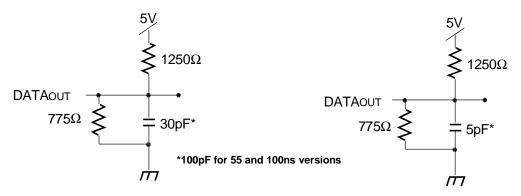
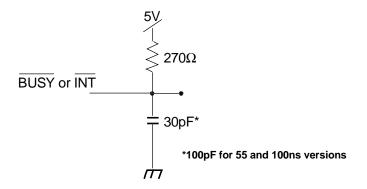


Figure 1. Output Test Load

Figure 2. Output Test Load (for thz, tLz, twz, and tow) \* including scope and jig



2689 drw 07

Figure 3. BUSY and INT AC Output Test Load

## AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range<sup>(3,5)</sup>

		7140X20 <sup>©</sup> 7140 Com'l Only Com		7140X20 <sup>(2)</sup> 7140X25		0X25 n'l &	7130 7140 Con Mili	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
trc	Read Cycle Time	20	_	25	_	35		ns
taa	Address Access Time	_	20	_	25	_	35	ns
tace	Chip Enable Access Time	_	20	_	25	_	35	ns
taoe	Output Enable Access Time	_	11	_	12	_	20	ns
tон	Output Hold from Address Change	3	_	3	_	3	_	ns
tLZ	Output Low-Z Time <sup>(1,4)</sup>	0	_	0	_	0	_	ns
thz	Output High-Z Time <sup>(1,4)</sup>	_	10	_	10	_	15	ns
tpu	Chip Enable to Power Up Time (4)	0	_	0	_	0	_	ns
tPD	Chip Disable to Power Down Time <sup>(4)</sup>		20		25		35	ns

2689 tbl 09a

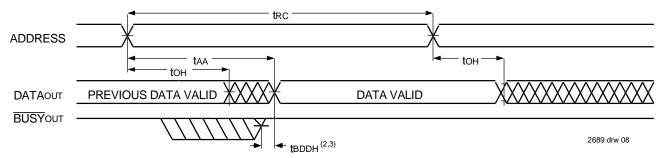
		7130X55 7140X55 Com'l, Ind & Military		7130X100 7140X100 Com'l, Ind & Military			
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit	
READ CYCLE							
trc	Read Cycle Time	55	_	100		ns	
taa	Address Access Time	_	55	_	100	ns	
tace	Chip Enable Access Time	-	55	_	100	ns	
taoe	Output Enable Access Time	-	25	_	40	ns	
tон	Output Hold from Address Change	3	_	10	-	ns	
tLZ	Output Low-Z Time <sup>(1,4)</sup>	5	_	5	_	ns	
tHZ	Output High-Z Time <sup>(1,4)</sup>	_	25	_	40	ns	
tpu	Chip Enable to Power Up Time <sup>(4)</sup>	0	_	0	_	ns	
tpd	Chip Disable to Power Down Time <sup>(4)</sup>	_	50		50	ns	

#### NOTES:

2689 tbl 09b

- 1. Transition is measured 0mV from Low or High-impedance voltage Output Test Load (Figure 2).
- PLCC, TQFP and STQFP packages only.
- 3. 'X' in part numbers indicates power rating (SA or LA).
- 4. This parameter is guaranteed by device characterization, but is not production tested.
- 5. Industrial temperature: for other speeds, packages and powers contact your sales office.

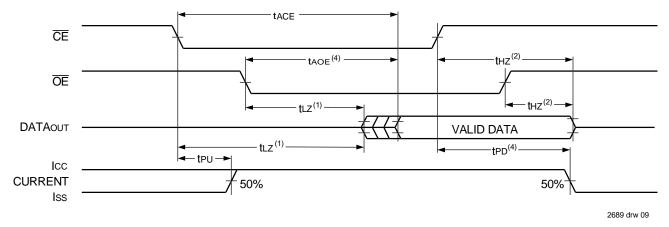
## Timing Waveform of Read Cycle No. 1, Either Side<sup>(1)</sup>



#### NOTES:

- 1.  $R/\overline{W} = V_{IH}$ ,  $\overline{CE} = V_{IL}$ , and is  $\overline{OE} = V_{IL}$ . Address is valid prior to the coincidental with  $\overline{CE}$  transition LOW.
- 2. tbbb delay is required only in the case where the opposite port is completing a write operation to the same the address location. For simultaneous read operations, BUSY has no relationship to valid output data.
- 3. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA, and tBDD.

## Timing Waveform of Read Cycle No. 2, Either Side<sup>(3)</sup>



#### NOTES

- 1. Timing depends on which signal is asserted last,  $\overline{\text{OE}}$  or  $\overline{\text{CE}}$ .
- 2. Timing depends on which signal is deaserted first,  $\overline{\text{OE}}$  or  $\overline{\text{CE}}$ .
- 3.  $R/\overline{W} = V_{IH}$  and  $\overline{OE} = V_{IL}$ , and the address is valid prior to or coincidental with  $\overline{CE}$  transition LOW.
- 4. Start of valid data depends on which timing becomes effective last tage, ta

AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range<sup>(5,6)</sup>

		7130X20 <sup>(2)</sup> 7130X25 7140X20 <sup>(2)</sup> 7140X25 Com'l Only Com'l & Military		7130X35 7140X35 Com'l & Military				
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE								
twc	Write Cycle Time <sup>(3)</sup>	20	_	25	_	35	_	ns
tew	Chip Enable to End-of-Write	15	_	20	_	30	-	ns
taw	Address Valid to End-of-Write	15		20	-	30	1	ns
tas	Address Set-up Time	0	_	0		0	1	ns
twp	Write Pulse Width <sup>(4)</sup>	15	_	15	-	25	1	ns
twr	Write Recovery Time	0	_	0		0	1	ns
tow	Data Valid to End-of-Write	10	_	12		15	1	ns
tHZ	Output High-Z Time <sup>(1)</sup>		10	_	10		15	ns
tDH	Data Hold Time	0	_	0	-	0	1	ns
twz	Write Enable to Output in High-Z <sup>(1)</sup>		10	_	10		15	ns
tow	Output Active from End-of-Write <sup>(1)</sup>	0	_	0	-	0	_	ns

2689 tbl 10a

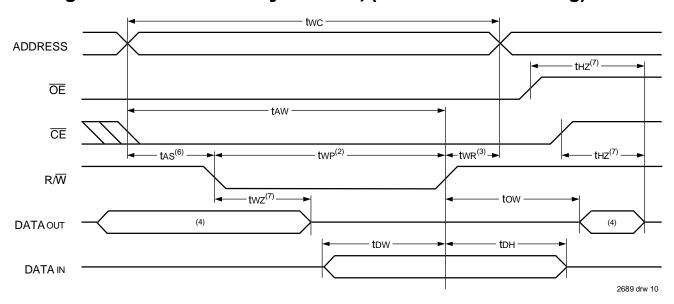
		7140 Com	0X55 0X55 '1, Ind litary	7130X100 7140X100 Com'l, Ind & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
WRITE CYCLI	<u> </u>					
twc	Write Cycle Time <sup>(3)</sup>	55	_	100	_	ns
tew	Chip Enable to End-of-Write	40 —				ns
taw	Address Valid to End-of-Write	40	_	90	_	ns
tas	Address Set-up Time	0	_	0	_	ns
twp	Write Pulse Width <sup>(4)</sup>	30	_	55	_	ns
twr	Write Recovery Time	0	_	0	_	ns
tow	Data Valid to End-of-Write	20	_	40	_	ns
tHZ	Output High-Z Time <sup>(1)</sup>	_	25	_	40	ns
tDH	Data Hold Time	0	_	0	_	ns
twz	Write Enable to Output in High-Z <sup>(1)</sup>	_	25		40	ns
tow	Output Active from End-of-Write <sup>(1)</sup>	0	0 — 0			ns

#### NOTES:

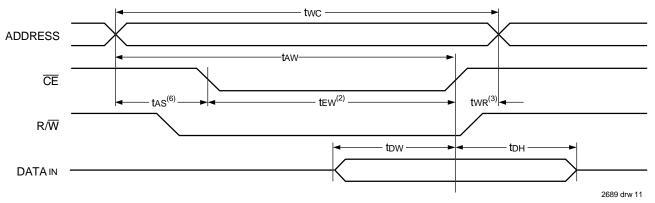
2689 tbl 10b

- 1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2). This parameter is guaranteed by device characterization but is not production tested.
- 2. PLCC, TQFP and STQFP packages only.
- 3. For MASTER/SLAVE combination, two = tbaa + twp, since R/ $\overline{W}$  = VIL must occur after tbaa.
- 4. If  $\overline{OE}$  is LOW during a  $R/\overline{W}$  controlled write cycle, the write pulse width must be the larger of twp or (twz + tbw) to allow the I/O drivers to turn off data to be placed on the bus for the required tbw. If  $\overline{OE}$  is HIGH during a R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 5. 'X' in part numbers indicates power rating (SA or LA).
- 6. Industrial temperature: for other speeds, packages and powers contact your sales office.

## Timing Waveform of Write Cycle No. 1, (R/W Controlled Timing)(1,5,8)



## Timing Waveform of Write Cycle No. 2, (CE Controlled Timing)(1,5)



#### NOTES:

- 1.  $R/\overline{W}$  or  $\overline{CE}$  must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of  $\overline{CE} = V_{IL}$  and  $R/\overline{W} = V_{IL}$ .
- 3. twn is measured from the earlier of  $\overline{\text{CE}}$  or  $\text{R/}\overline{\text{W}}$  going HIGH to the end of the write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the RW LOW transition, the outputs remain in the HIGH impedance state.
- 6. Timing depends on which enable signal (CE or R/W) is asserted last.
- 7. This parameter is determined be device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If  $\widetilde{OE}$  is LOW during a  $R\overline{W}$  controlled write cycle, the write pulse width must be the larger of two or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If  $\widetilde{OE}$  is HIGH during a  $R\overline{W}$  controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified two.

## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(7,9)</sup>

		7130X20 <sup>(1)</sup> 7140X20 <sup>(1)</sup> Com'l Only		7130X25 7140X25 Com'l & Military		7130X35 7140X35 Com'l & Military			
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	
BUSY TIMING (For MASTER IDT 7130)									
†BAA	BUSY Access Time from Address	_	20	_	20		20	ns	
tbda .	BUSY Disable Time from Address	ı	20		20	I	20	ns	
tBAC	BUSY Access Time from Chip Enable — 20						20	ns	
tBDC	BUSY Disable Time from Chip Enable	_	20	_	20		20	ns	
twn	Write Hold After BUSY <sup>(6)</sup>	12		15	_	20	_	ns	
twdd	Write Pulse to Data Delay <sup>(2)</sup>	-	40	-	50		60	ns	
todd	Write Data Valid to Read Data Delay <sup>(2)</sup>	-	30		35		35	ns	
taps	Arbitration Priority Set-up Time <sup>(3)</sup>	5		5	_	5	_	ns	
tBDD	BUSY Disable to Valid Data <sup>(4)</sup>	-	25		35		35	ns	
BUSY INPUT TIMING (For SLAVE IDT 7140)									
twB	Write to BUSY Input <sup>(5)</sup>	0		0	_	0	-	ns	
twn	Write Hold After BUSY <sup>(6)</sup>	12		15	_	20	_	ns	
twdd	Write Pulse to Data Delay <sup>(2)</sup>	_	40		50		60	ns	
todd	Write Data Valid to Read Data Delay <sup>(2)</sup>	_	30	_	35		35	ns	

2689 tbl 11 a

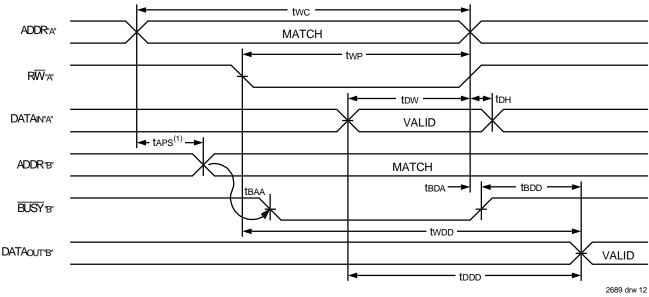
		Com	)X55 )X55 'I, Ind litary	7130X100 7140X100 Com'l, Ind & Military				
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit		
<b>BUSY</b> TIMING	(For MASTER IDT 7130)							
<b>t</b> BAA	BUSY Access Time from Address]		30	_	50	ns		
tBDA	BUSY Disable Time from Address	_	30	_	50	ns		
<b>t</b> BAC	BUSY Access Time from Chip Enable	_	30	_	50	ns		
tBDC	BUSY Disable Time from Chip Enable	_	30	_	50	ns		
twn	Write Hold After BUSY <sup>(6)</sup>	20		20	_	ns		
twdd	Write Pulse to Data Delay <sup>(2)</sup>	_	80	_	120	ns		
todd	Write Data Valid to Read Data Delay <sup>(2)</sup>	_	55	_	100	ns		
taps	Arbitration Priority Set-up Time <sup>(3)</sup>	5		5	_	ns		
tBDD	BUSY Disable to Valid Data <sup>(4)</sup>	_	55	_	65	ns		
<b>BUSY</b> INPUT 1	BUSY INPUT TIMING (For SLAVE IDT 7140)							
twB	Write to BUSY Input <sup>(5)</sup>	0		0	_	ns		
twн	Write Hold After BUSY <sup>(6)</sup>	20		20	_	ns		
twdd	Write Pulse to Data Delay <sup>(2)</sup>	_	80	_	120	ns		
todd	Write Data Valid to Read Data Delay <sup>(2)</sup>	_	55	_	100	ns		

#### NOTES

2689 tbl 11b

- 1. PLCC, TQFP and STQFP packages only.
- 2. Port-to-port delay through RAM cells from the writing port to the reading port, refer to "Timing Waveform of Write with Port -to-Port Read and BUSY."
- 3. To ensure that the earlier of the two ports wins.
- 4. tbdd is a calculated parameter and is the greater of 0, twdd twp (actual) or tddd tdw (actual).
- 5. To ensure that a write cycle is inhibited on port 'B' during contention on port 'A'.
- 6. To ensure that a write cycle is completed on port 'B' after contention on port 'A'.
- 7. 'X' in part numbers indicates power rating (S or L).
- 8. Industrial temperature: for other speeds, packages and powers contact your sales office.

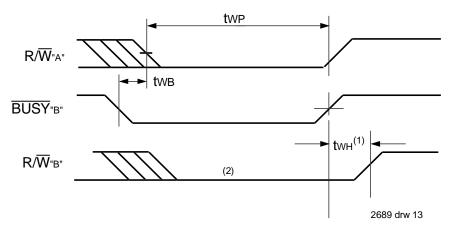
## Timing Waveform of Write with Port-to-Port Read and BUSY (2,3,4)



#### NOTES:

- 1. To ensure that the earlier of the two ports wins. tBDD is ignored for slave (IDT7140).
- 2.  $\overline{CE}L = \overline{CE}R = VIL$
- 3.  $\overline{OE} = V_{IL}$  for the reading port.
- 4. All timing is the same for the left and right ports. Port 'A' may be either the left or right port. Port "B" is opposite from port "A".

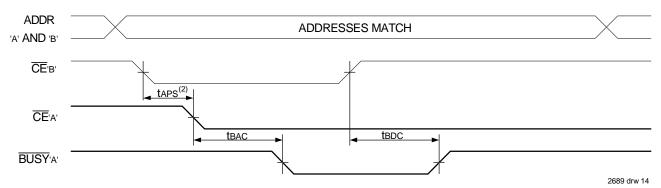
## Timing Waveform of Write with $\overline{BUSY}^{(3)}$



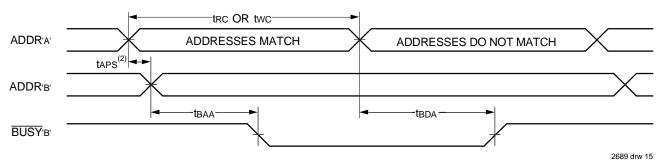
#### NOTES:

- 1. twn must be met for both BUSY Input (IDT7140, slave) or Output (IDT7130 master).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is oppsite from port "A".

## Timing Waveform of BUSY Arbitration Controlled by CE Timing(1)



## Timing Waveform by $\overline{\rm BUSY}$ Arbitration Controlled by Address Match Timing<sup>(1)</sup>



#### NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. If taps is not satisified, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted (7130 only).

## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(2,3)</sup>

	<u> </u>								
		7140	X20 <sup>(1)</sup> X20 <sup>(1)</sup> I Only	7140 Con	)X25 )X25 n'l & tary	7130 7140 Con Mili			
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit	
INTERRUPT T	INTERRUPT TIMING								
tas	Address Set-up Time	0	_	0	_	0	_	ns	
twr	Write Recovery Time	0	_	0	_	0	_	ns	
tins	Interrupt Set Time	_	20	_	25	_	25	ns	
tinr	Interrupt Reset Time	_	20	_	25	_	25	ns	

#### NOTES:

- 1. PLCC, TQFP and STQFP package only.
- 2. 'X' in part numbers indicates power rating (SA or LA).
- 3. Industrial temperature: for other speeds, packages and powers contact your sales office.

2689 tbl 12a

## AC Electrical characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1,2)</sup>

		7140	)X55 )X55 I, Ind litary	7130 7140 Com & Mi						
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit				
INTERRUPT T	INTERRUPT TIMING									
tas	Address Set-up Time	0	_	0		ns				
twr	Write Recovery Time	0	_	0		ns				
tins	Interrupt Set Time		45	_	60	ns				
tinr	Interrupt Reset Time		45	_	60	ns				

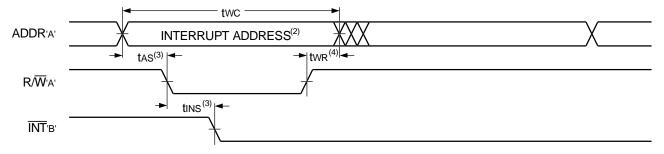
#### NOTES:

2689 tbl 12b

- 1. 'X' in part numbers indicates power rating (SA or LA).
- 2. Industrial temperature: for other speeds, packages and powers contact your sales office.

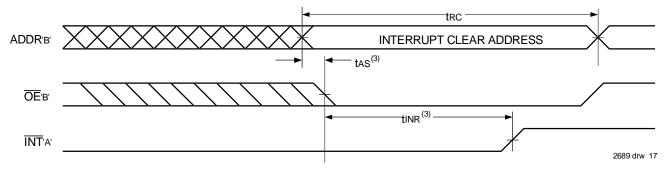
## Timing Waveform of Interrupt Mode<sup>(1)</sup>

### **INT** Set:



2689 drw 16

#### **INT** Clear:



#### NOTES:.

- 1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 2. See Interrupt Truth Table II.
- 3. Timing depends on which enable signal  $(\overline{CE} \text{ or } R/\overline{W})$  is asserted last.
- 4. Timing depends on which enable signal ( $\overline{\text{CE}}$  or  $R/\overline{\text{W}}$ ) is de-asserted first.

#### **Truth Tables**

### Truth Table I — Non-Contention Read/Write Control<sup>(4)</sup>

Inputs <sup>(1)</sup>				
R/W	CE	Œ	<b>D</b> 0-7	Function
Х	Н	Х	Z	Port Disabled and in Power-Down Mode, ISB2 or ISB4
Х	Н	Х	Z	CER = CEL = VH, Power-Down Mode, ISB1 or ISB3
L	L	Х	DATAIN	Data on Port Written into Memory <sup>(2)</sup>
Н	L	L	DATAоит	Data in Memory Output on Port <sup>(3)</sup>
Н	L	Н	Z	High Impedance Outputs

#### NOTES:

- 1. A0L A10L A0R A10R.
- If BUSY = L, data is not written.
   If BUSY = L, data may not be valid, see twop and topp timing.
- 4. 'H' = VIH, 'L' = VIL, 'X' = DON'T CARE, 'Z' = HIGH IMPEDANCE

## Truth Table II — Interrupt Flag<sup>(1,4)</sup>

	Left Port Rig						Right Por	t		
R/WL	CEL	ŌĒL	A9L-A0L	ĪNT∟	R/W̄R	CER	ŌĒ <sub>R</sub>	A9R-A0R	ĪÑ₹R	Function
L	L	Х	3FF	Х	Х	Х	Х	Х	L <sup>(2)</sup>	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	3FF	H <sup>(3)</sup>	Reset Right INTR Flag
Х	Х	Х	Х	L <sup>(3)</sup>	L	L	Х	3FE	Х	Set Left INTL Flag
Х	L	L	3FE	H <sup>(2)</sup>	Х	Х	Х	X	Х	Reset Left INT <sub>L</sub> Flag

#### NOTES:

2689 tbl 14

2689 tbl 13

- 1. Assumes  $\overline{BUSY}L = \overline{BUSY}R = VIH$
- 2. If  $\overline{\text{BUSY}}L = \text{VIL}$ , then No Change.
- 3. If  $\overline{\text{BUSY}}R = \text{VIL}$ , then No Change.
- 4. 'H' = HIGH,' L' = LOW,' X' = DON'T CARE

## Truth Table III — Address $\overline{\text{BUSY}}$ Arbitration

	ln	puts	Out	puts	
CEL	<b>ՇĒ</b> R	Aol-A9l Aor-A9r	BUSY <sub>L</sub> (1)	BUSY <sub>R</sub> (1)	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit <sup>(3)</sup>

**NOTES:** 2689 tbl 15

- Pins BUSY<sub>L</sub> and BUSY<sub>R</sub> are both outputs for IDT7130 (master). Both are inputs for IDT7140 (slave). BUSY<sub>X</sub> outputs on the IDT7130 are open drain, not push-pull outputs. On slaves the BUSY<sub>X</sub> input internally inhibits writes.
- 'L' if the inputs to the opposite port were stable prior to the address and enable inputs
  of this port. 'H' if the inputs to the opposite port became stable after the address and
  enable inputs of this port. If taps is not met, either BUSYL or BUSYR = LOW will
  result. BUSYL and BUSYR outputs can not be LOW simultaneously.
- Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

### **Functional Description**

The IDT7130/IDT7140 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7130/IDT7140 has an automatic power down feature controlled by  $\overline{\text{CE}}$ . The  $\overline{\text{CE}}$  controls onchip power down circuitry that permits the respective port to go into a standby mode when not selected ( $\overline{\text{CE}}$  = ViH). When a port is enabled, access to the entire memory array is permitted.

### **Interrupts**

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ( $\overline{\text{INT}}\text{L}$ ) is asserted when the right port writes to memory location 3FE (HEX), where a write is defined as the  $\overline{\text{CE}}\text{R} = R/\overline{\text{WR}} = \text{VIL}$  per Truth Table II. The left port clears the interrupt by access address location 3FE access when  $\overline{\text{CE}}\text{L} = \overline{\text{OE}}\text{L} = \text{VIL}$ , R/W is a "don't care". Likewise, the right port interrupt flag ( $\overline{\text{INT}}\text{R}$ ) is asserted when the left port writes to memory location 3FF (HEX) and to clear the interrupt flag ( $\overline{\text{INT}}\text{R}$ ), the right port must access the memory location 3FF. The message (8 bits) at 3FE or 3FF is user-defined, since it is an addressable SRAM location. If the interrupt function is not used, address locations 3FE and 3FF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table II for the interrupt operation.

### **Busy Logic**

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a BUSY indication, the write signal is gated internally to prevent the write from proceeding.

The use of  $\overline{\text{BUSY}}$  logic is not required or desirable for all applications. In some cases it may be useful to logically OR the  $\overline{\text{BUSY}}$  outputs together and use any  $\overline{\text{BUSY}}$  indication as an interrupt source to flag the event of an illegal or illogical operation. In slave mode the  $\overline{\text{BUSY}}$  pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the  $\overline{\text{BUSY}}$  pins HIGH. If desired, unintended write operations can be prevented to a port by tying the  $\overline{\text{BUSY}}$  pin for that port LOW.

The BUSY outputs on the IDT7130 RAM (Master) are open drain type outputs and require open drain resistors to operate. If these

RAMs are being expanded in depth, then the BUSY indication for the resulting array does not require the use of an external AND gate.

## Width Expansion with Busy Logic Master/Slave Arrays

When expanding an RAM array in width while using busy logic, one master part is used to decide which side of the RAM array will receive a busy indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the busy signal as a write inhibit signal. Thus on the IDT7130/IDT7140 RAMs the  $\overline{\text{BUSY}}$  pin is an output if the part is Master (IDT7130), and the  $\overline{\text{BUSY}}$  pin is an input if the part is a Slave (IDT7140) as shown in Figure 3.

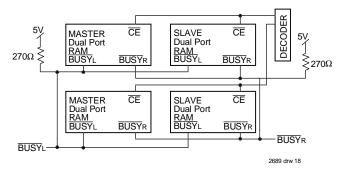
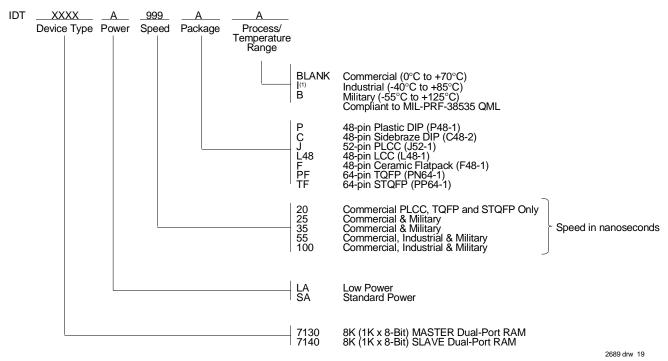


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT7130 (Master) and IDT7140 (Slave)RAMs.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating busy on one side of the array and another master indicating busy on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The  $\overline{BUSY}$  arbitration, on a Master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a  $\overline{BUSY}$  flag to be output from the master before the actual write pulse can be initiated with either the  $R/\overline{W}$  signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

### **Ordering Information**



#### NOTE:

Industrial temperature range is available on selected PLCC packages in standard temperature.
 For other speeds, packages and powers contact your sales office.

## **Datasheet Document History**

3/15/99: Initiated datasheet document history

Converted to new format

Cosmetic and typographical corrections

Pages 2 and 3 Added additional notes to pin configurations

6/8/99: Changed drawing format

8/2/99: Page 2 Corrected package number in note 3 9/29/99: Page 2 Fixed pin 1 in DIP pin configuration

11/10/99: Replaced IDT logo

6/23/00: Page 4 Increased storage temperature parameters

Clarified Taparameter

Page 5 DC Electrical parameters—changed wording from "open" to "disabled"

Changed ±500mV to 0mV in notes



CORPORATE HEADQUARTERS

2975 Stender Way Santa Clara, CA 95054 for SALES:

800-345-7015 or 408-727-5166

fax: 408-492-8674 www.idt.com *for Tech Support:* 831-754-4613

DualPortHelp@idt.com

The IDT logo is a registered trademark of Integrated Device Technology, Inc.